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Bipolar Power Transistors 100 V, 3.0 A, Low $V_{CE(sat)}$ PNP Transistor

NSV1C300CT

ON Semiconductor's e^2PowerEdge family of low $V_{CE(sat)}$ transistors are surface mount devices featuring ultra−low saturation voltage, $V_{CE(sat)}$, and high current gain capability. These are designed for use in lower voltage, high speed switching applications where affordable efficient energy control is important.

Housed in an ultra slim LFPAK4 5x6 package, typical applications are DC−DC converters and power management in portable and battery powered products such as cellular and cordless phones, digital cameras and MP3 players where PCB space is at a premium. The LFPAK4 5x6 package also contains wettable flanks which are a requirement for the automotive industry's optical inspection methods that are implemented in end applications such as air bag deployment, powertrain control units, and instrument clusters.

Features

- Complement to NSS1C301CT
- Ultra−slim LFPAK4 Package (5 x 6 mm) with Wettable Flanks
- NSV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC−Q101 Qualified and PPAP Capable
- These Devices are Pb−Free, Halogen Free/BFR Free and are RoHS Compliant

MAXIMUM RATINGS (T_C = 25°C unless otherwise noted)

Rating	Symbol	Value	Unit
Collector−Emitter Voltage	V_{CEO}	−100	Vdc
Collector−Base Voltage	V_{CBO}	−140	Vdc
Emitter−Base Voltage	V_{EB}	−6.0	Vdc
Base Current − Continuous	I_B	−0.5	Adc
Collector Current − Continuous	I_C	−3.0	Adc
Collector Current − Peak	I_{CM}	−6.0	A
Total Power Dissipation Total P_D @ T_A = 25°C (Note 1) Total P_D @ T_A = 25°C (Note 2)	P_D	 5.0 1.0	W
Operating and Storage Junction Temperature Range	T_J, T_{stg}	−55 to +150	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. Mounted on 1″ sq. (645 sq. mm) Collector pad on FR−4 bd material.
2. Mounted on 0.012″ sq. (7.6 sq. mm) Collector pad on FR−4 bd material.

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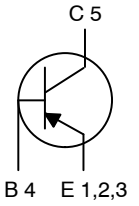
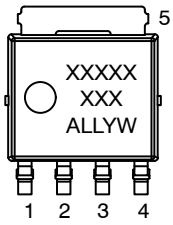
PNP TRANSISTOR
−3.0 AMPERES
−100 VOLTS



Schematic

LFPAK4 5x6
CASE 760AB

MARKING DIAGRAM



(Top View)

XXXXXX	= Specific Device Code
A	= Assembly Location
LL	= Wafer Lot
Y	= Year
W	= Work Week

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 2 of this data sheet.

ORDERING INFORMATION

Device	Package	Shipping†
NSS1C300CTWG	LFPAK4 5x6 (Pb−Free)	3,000 / Tape & Reel
NSV1C300CTWG*	LFPAK 5x6 (Pb−Free)	3,000 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.
*NSV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC−Q101 Qualified and PPAP Capable

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction−to−Case Junction−to−Ambient on 1” sq. (645 sq. mm) Collector pad on FR−4 bd material Junction−to−Ambient on 0.012” sq. (7.6 sq. mm) Collector pad on FR−4 bd material	 $R_{\theta JA}$ $R_{\theta JA}$	 40 120	°C/W

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Typ	Max	Unit
OFF CHARACTERISTICS					
Collector − Emitter Breakdown Voltage (I_C = −10 mAdc, I_B = 0)	$V_{(BR)CEO}$	−100	−	−	Vdc
Collector − Base Breakdown Voltage (I_C = −0.1 mAdc, I_E = 0)	$V_{(BR)CBO}$	−140	−	−	Vdc
Emitter − Base Breakdown Voltage (I_E = −0.1 mAdc, I_C = 0)	$V_{(BR)EBO}$	−6.0	−	−	Vdc
Collector Cutoff Current (V_{CB} = −140 Vdc, I_E = 0)	I_{CBO}	−	−	−0.1	μAdc
Emitter Cutoff Current (V_{EB} = −6.0 Vdc)	I_{EBO}	−	−	−0.1	μAdc
ON CHARACTERISTICS					
DC Current Gain (Note 3) (I_C = −0.1 A, V_{CE} = −2.0 V) (I_C = −0.5 A, V_{CE} = −2.0 V) (I_C = −1.0 A, V_{CE} = −2.0 V) (I_C = −3.0 A, V_{CE} = −2.0 V)	h_{FE}	 180 180 120 50	 − − − −	 − − 500 −	−
Collector − Emitter Saturation Voltage (Note 3) (I_C = −0.1 A, I_B = −10 mA) (I_C = −1.0 A, I_B = −0.100 A) (I_C = −2.0 A, I_B = −0.200 A) (I_C = −3.0 A, I_B = −0.300 A)	$V_{CE(sat)}$	 − − − −	 − − − −	 −0.070 −0.150 −0.250 −0.400	V
Base − Emitter Saturation Voltage (Note 3) (I_C = −1.0 A, I_B = −0.1 A)	$V_{BE(sat)}$	−	−	−1.0	V
Base − Emitter Turn−on Voltage (Note 3) (I_C = −1.0 A, V_{CE} = −2.0 V)	$V_{BE(on)}$	−	−	−0.900	V
Cutoff Frequency (I_C = −500 mA, V_{CE} = −10 V, f = 100 MHz)	f_T	−	100	−	MHz
Input Capacitance (V_{EB} = −5.0 V, f = 1.0 MHz)	Cibo	−	360	−	pF
Output Capacitance (V_{CB} = −10 V, f = 1.0 MHz)	Cobo	−	60	−	pF

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.
3. Pulsed Condition: Pulse Width = 300 msec, Duty Cycle ≤ 2%.

TYPICAL CHARACTERISTICS

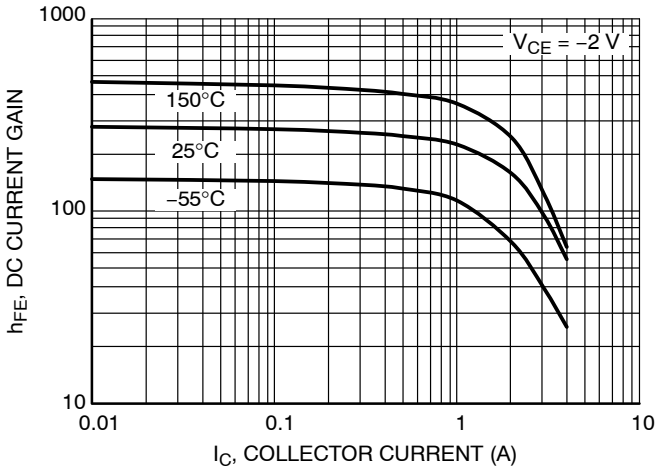


Figure 1. DC Current Gain

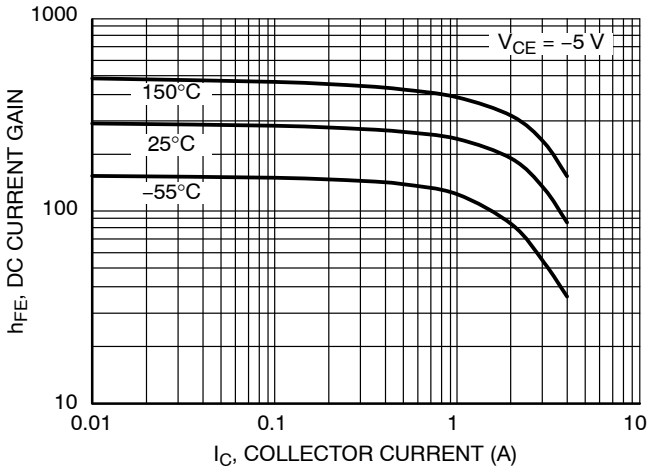


Figure 2. DC Current Gain

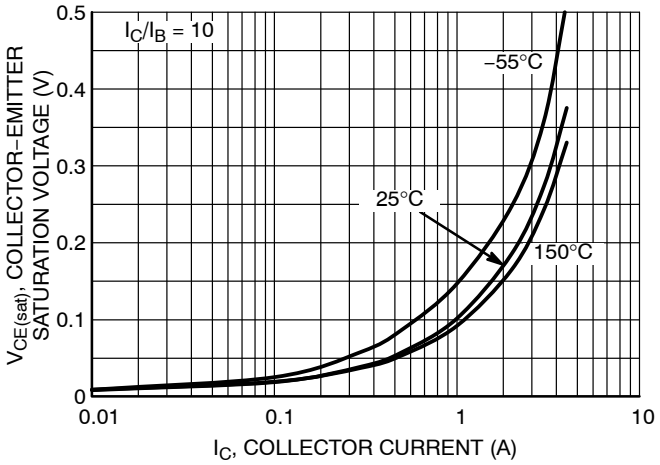


Figure 3. Collector−Emitter Saturation Voltage

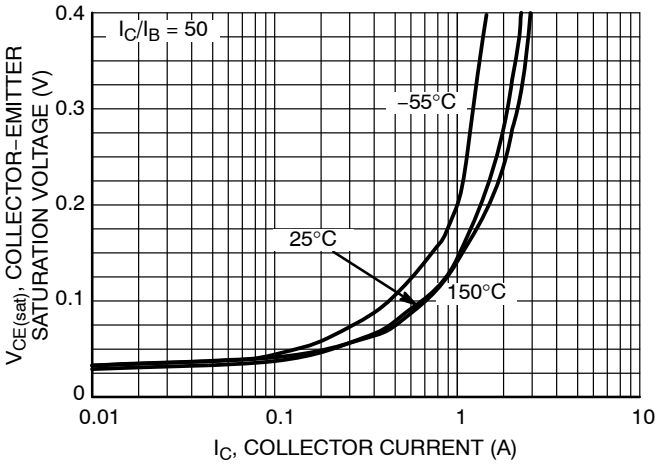


Figure 4. Collector−Emitter Saturation Voltage

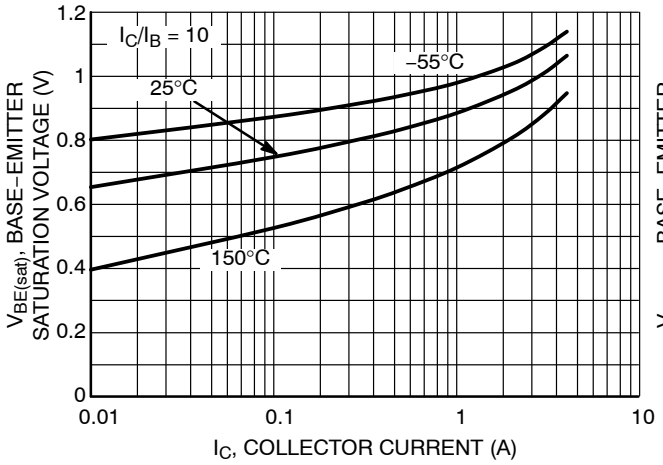


Figure 5. Base−Emitter Saturation Voltage

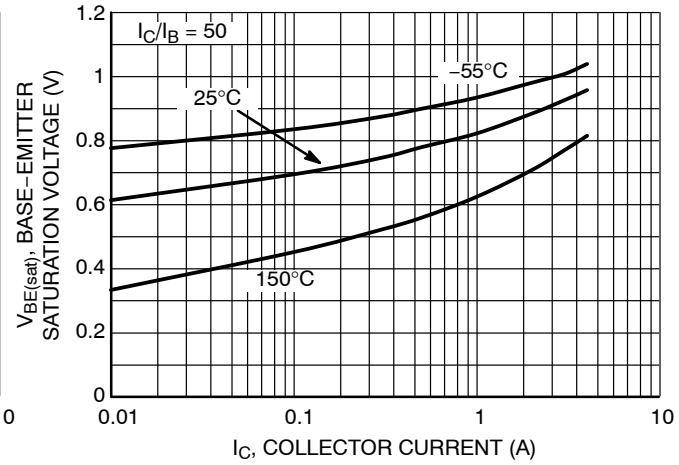


Figure 6. Base−Emitter Saturation Voltage

TYPICAL CHARACTERISTICS

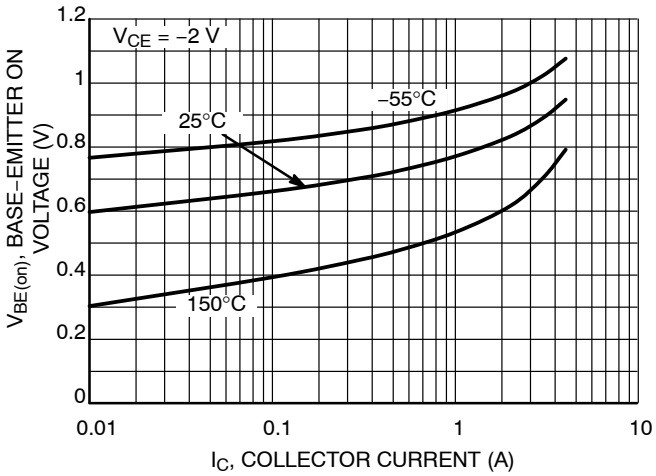


Figure 7. Base−Emitter On Voltage

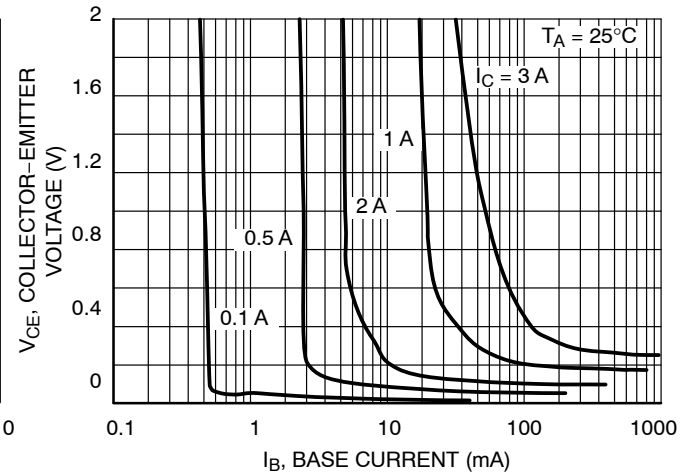


Figure 8. Collector Saturation Region

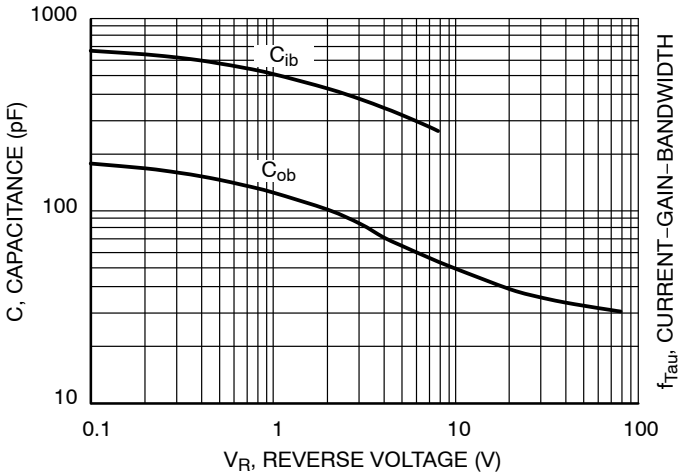


Figure 9. Capacitance

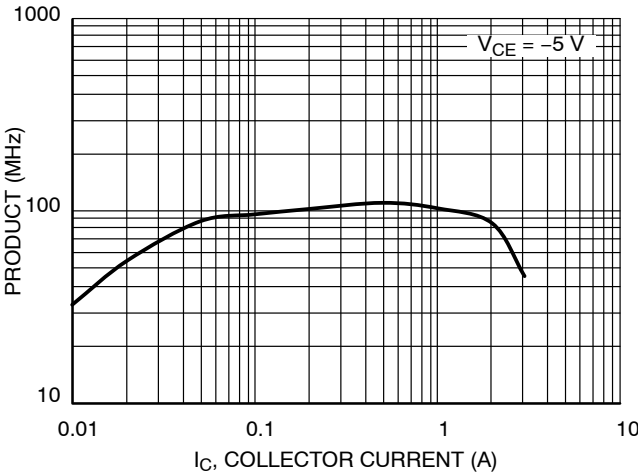


Figure 10. Current−Gain−Bandwidth Product

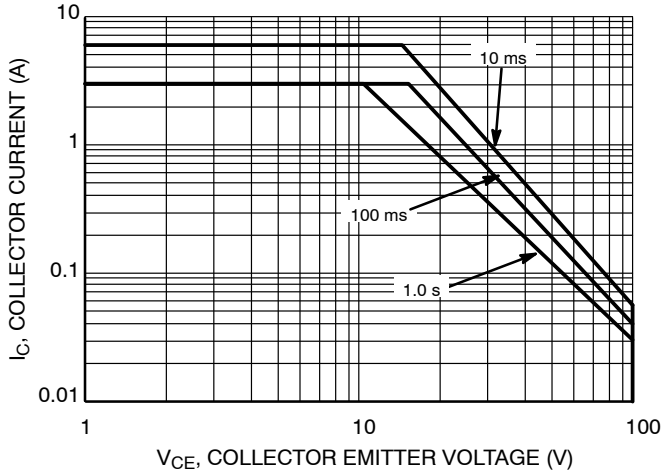


Figure 11. Safe Operating Area

TYPICAL CHARACTERISTICS

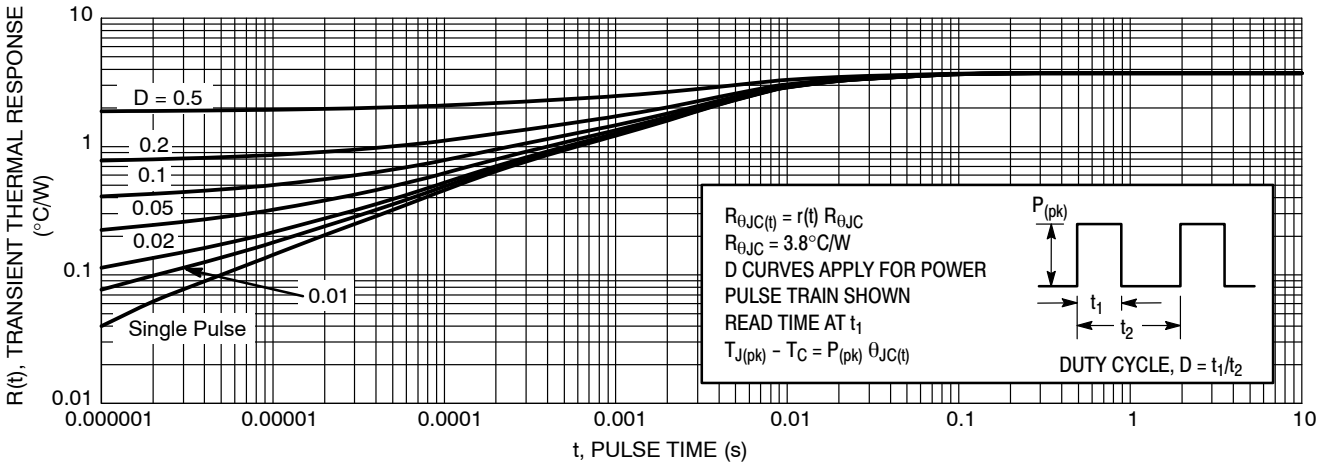
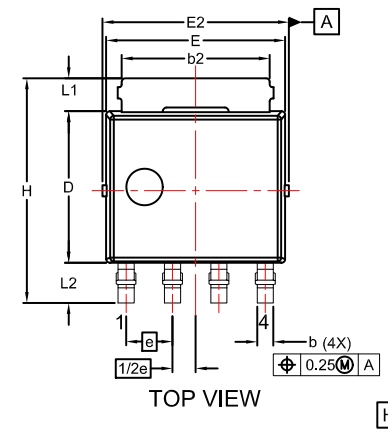


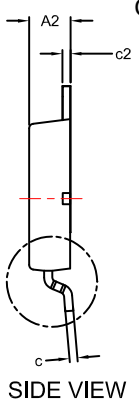
Figure 12. Typical Transient Thermal Response, Junction−to−Case

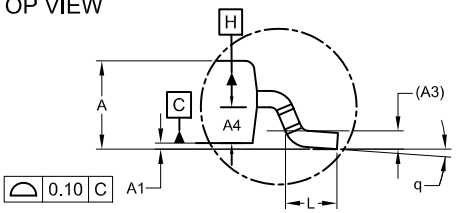
NSV1C300CT

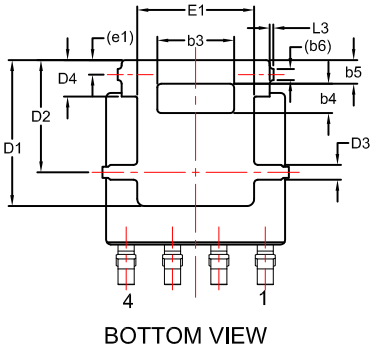
PACKAGE DIMENSIONS

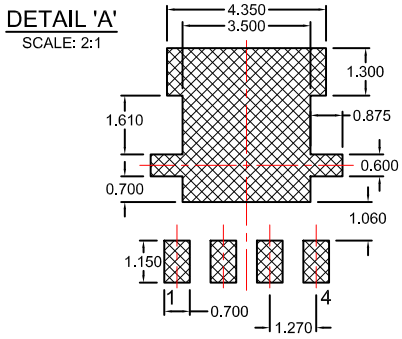
LFPAK4 5x6
CASE 760AB
ISSUE C











*FOR ADDITIONAL INFORMATION ON OUR PB-FREE STRATEGY AND SOLDERING DETAILS, PLEASE DOWNLOAD THE ON SEMICONDUCTOR SOLDERING AND MOUNTING TECHNIQUES REFERENCE MANUAL, SOLDERRM/D.

NOTES:
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR BURRS. MOLD FLASH PROTRUSIONS OR GATE BURRS SHALL NOT EXCEED 0.150mm PER SIDE.
4. DIMENSIONS D AND E ARE DETERMINED AT THE OUTERMOST EXTREMES OF THE PLASTIC BODY.
5. DATUMS A AND B ARE DETERMINED AT DATUM PLANE H.

UNIT IN MILLIMETER			
DIM	MIN	NOM	MAX
A	1.10	1.20	1.30
A1	0.00	0.08	0.15
A2	1.10	1.15	1.20
A3		0.25 REF	
A4	0.45	0.50	0.55
b	0.40	0.45	0.50
b2	3.80	4.10	4.40
b3	2.00	2.10	2.20
b4	0.70	0.80	0.90
b5	0.55	0.65	0.75
b6		0.31 REF	
c	0.19	0.22	0.25
c2	0.19	0.22	0.25
D	4.05	4.15	4.25
D1	3.80	4.00	4.20
D2	3.00	3.10	3.20
D3	0.30	0.40	0.50
D4	0.90	1.00	1.10
E	4.80	4.90	5.00
E1	3.10	3.20	3.30
E2	5.00	5.15	5.30
e		1.27 BSC	
1/2e		0.635 BSC	
e1		0.40 REF	
H	6.00	6.15	6.30
L	0.40	0.65	0.85
L1	0.80	0.90	1.00
L2	0.90	1.10	1.30
L3	0.00	0.10	0.20
q	0°	4°	8°

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